

accompanying pages separate from this amendment in accordance with 37 CFR § 1.121(b)(1)(iii).

Additional and/or alternate preferred processing can occur in accordance with any of our co-pending U.S. Patent Application Serial No. 09/476,516, filed on January 3, 2000, entitled "Chemical Vapor Deposition Methods Of Forming A High K Dielectric Layer And Methods Of Forming A Capacitor", listing Cem Basceri as inventor; U.S. Patent Application Serial No. 09/580,733, filed on May 26, 2000, entitled "Chemical Vapor Deposition Methods And Physical Vapor Deposition Methods", listing Cem Basceri as inventor; and U.S. Patent Application Serial No. 09/905,286, filed concurrently herewith, entitled "Chemical Vapor Deposition Methods Of Forming Barium Strontium Titanate Comprising Dielectric Layers", listing Cem Basceri and Nancy Alzola as inventors. Each of these is hereby fully incorporated by reference.